



Product data sheet

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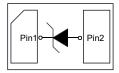


ESD56201DXX-MS

Semiconductor Compiance



DFN1610-2L



Circuit diagram

Descriptions

The ESD56201DXX-MS is a transient voltage suppressor designed to protect power interfaces. It is suitable to replace multiple discrete components in portable electronics.

The ESD56201DXX-MS is specifically designed to protect power lines.

The ESD56201DXX-MS is available in DFN1610-2L package. Standard products are Pb-free and Halogen-free.

Features

- Reverse stand-off voltage: 4.85V ~ 24V
- Surge protection according to IEC61000-4-5 see Table 4
- ESD protection according to IEC61000-4-2 ±30kV (contact and air discharge)
- Low clamping voltage
- Solid-state silicon technology

Applications

- Power supply protection
- Power management

Order information

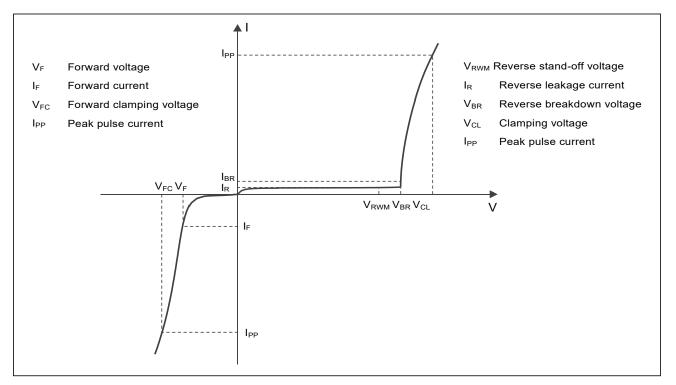
Device	Package	Shipping	Marking
ESD56201D04-MS	DFN1610-2L	3000/Tape&Reel	D4*
ESD56201D05-MS	DFN1610-2L	3000/Tape&Reel	I *
ESD56201D10-MS	DFN1610-2L	3000/Tape&Reel	J*
ESD56201D12-MS	DFN1610-2L	3000/Tape&Reel	K*
ESD56201D15-MS	DFN1610-2L	3000/Tape&Reel	L*
ESD56201D18-MS	DFN1610-2L	3000/Tape&Reel	S*
ESD56201D20-MS	DFN1610-2L	3000/Tape&Reel	N*



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Parameter	Symbol	Rating	Unit	
Peak pulse power (tp = 8/20µs)	P _{pk}	1800	W	
ESD according to IEC61000-4-2 air discharge	N/	±30	kV	
ESD according to IEC61000-4-2 contact discharge	- V _{ESD}	±30		
Junction temperature	TJ	125	°C	
Operating temperature	T _{OP}	-40~85	°C	
Lead temperature	TL	260	°C	
Storage temperature	T _{STG}	-55~150	°C	

Electrical characteristics (T_A = 25°C, unless otherwise noted)



Definitions of electrical characteristics



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P/N	Reverse Stand-off Voltage VRWM (V)	Breakdown voltage V _{BR} (V) I _{BR} = 1mA		Reverse leakage current I _{RM} (µA) at V _{RWM}		Forward voltage V _F (V) I _F = 20mA		Junction capacitance F = 1MHz, VR=0V (pF)		
	Max	Min	Тур	Max	Тур е	Max	Min	Мах	Тур	Мах
ESD56201D04-MS	4.85	5.2	5.7	6.2	-	5.0	0.45	1.25	1100	1300
ESD56201D05-MS	5.0	6.6	7.1	7.6	-	2.0	0.45	1.25	1050	1250
ESD56201D10-MS	10.0	10.7	11.3	12.3	-	0.1	0.45	1.25	545	650
ESD56201D12-MS	12.0	12.7	13.7	14.6	-	0.1	0.45	1.25	425	510
ESD56201D15-MS	15.0	16.0	17.5	19.0	-	0.1	0.45	1.25	325	350
ESD56201D18-MS	18.0	19.2	21.1	23.0	-	0.1	0.45	1.25	270	300
ESD56201D20-MS	20.0	21.4	23.2	25.0	-	0.1	0.45	1.25	250	275

Electrical characteristics (T_A = 25°C, unless otherwise noted)

	Rated peak pulse current I_{PP} (A) ¹⁾²⁾	Clamping voltage $V_{CL}(V)$ at IPP (A) ¹⁾²⁾		
P/N	Max.	Тур.	Max.	
ESD56201D04-MS	120	10.5	12.0	
ESD56201D05-MS	100	11.0	13.0	
ESD56201D10-MS	86	17.5	20.0	
ESD56201D12-MS	75	19.5	22.0	
ESD56201D15-MS	60	27.0	30.0	
ESD56201D18-MS	50	32.0	35.0	
ESD56201D20-MS	45	35.0	38.0	

Notes:

1 Non-repetitive current pulse, according to IEC61000-4-5. (8/20µs current waveform)

2 Non-repetitive current pulse, according to IEC61000-4-2.

3 Measured from pin 1 to pin 2.

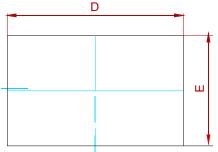


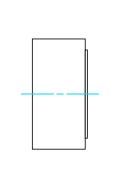
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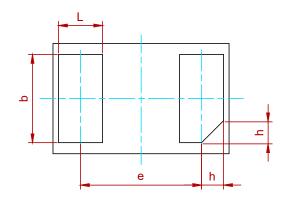
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RoHS

PACKAGE MECHANICAL DATA







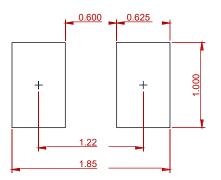
TOP VIEW



BOTTOM VIEW

Symbol	Dimensions in Millimeters				
Symbol	Min.	Тур.	Max.		
А	0.45	0.50	0.55		
A1	0.00	0.02	0.05		
с	0.15 Ref.				
b	0.75	0.80	0.85		
L	0.35	0.40	0.45		
D	1.55	1.60	1.65		
E	0.95	1.00	1.05		
e	1.10 BSC				
h	0.20 Ref.				

Recommend PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
ESD56201DXX-MS	DFN1610-2L	3000



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